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ABSTRACT

[0040] A method for reducing or preventing contamination or oxidation of copper surfaces included in semiconductor process wafers including providing a semiconductor wafer including copper features having newly formed process surfaces following a semiconductor manufacturing process forming the newly formed process surfaces; exposing the process surfaces to an alkaline solution for a period of time sufficient to chemically modify the newly formed process surfaces prior to substantial exposure of the process surfaces to a contaminating or oxidizing atmosphere; and, placing the semiconductor wafer in a semiconductor wafer holding environment in queue for subsequent semiconductor manufacturing processes.